

# COMMODORE SEMICONDUCTOR GROUP

a division of Commodore Business Machines, Inc. 950 Rittenhouse Road, Notristown, PA 19403 • 215/666-7950 • TWX 510-660-4168

### 6510 MICROPROCESSOR WITH I/O

#### DESCRIPTION

The 6510 is a low-cost microprocessor capable of solving a broad range of small-systems and peripheral-control problems at minimum cost to the user.

An 8-bit Bi-Directional I/O Port is located on-chip with the Output Register at Address 0001 and the Data-Direction Register at Address 0000. The I/O Port is bit-by-bit programmable.

The Three-State sixteen-bit Address Bus allows Direct Memory Accessing (DMA) and multi-processor systems sharing a common memory.

The internal processor architecture is identical to the Commodore Semiconductor Group 6502 to provide software compatibility.

#### FEATURES OF THE 6510...

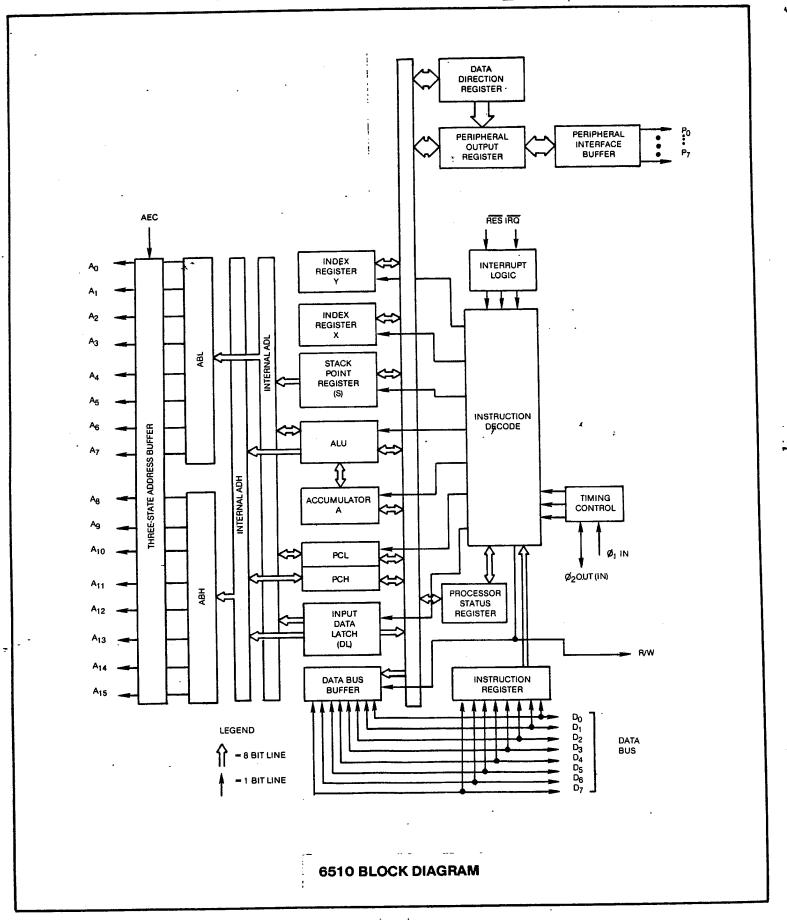
- 8-Bit Bi-Directional I/O Port
- Single +5 volt supply
- HMOS, silicon gate, depletion load technology
- Eight bit parallel processing
- 56 Instructions
- Decimal and binary arithmetic
- Thirteen addressing modes
- True indexing capability
- Programmable stack pointer
- Variable length stack
- Interrupt capability
- 8 Bit Bi-Directional Data Bus
- Addressable memory range of up to 65K bytes
- Direct memory access capability
- Bus compatible with M6800
- Pipeline architecture
- 1 MHz, 2MHz and 3 MHz operation
- Use with any type or speed memory
- 4 MHz operation availability expected in 1986.
- Also available in two phase clock input format.

#### PIN CONFIGURATION

				-	
	RES	1		40	Ø <sub>2</sub> OUT
	Ø1 IN	2		39	R/W
	ĪRQ	3		38	DB <sub>0</sub>
	AEC	4		37	$DB_1$
	Vcc	5		36	DB <sub>2</sub>
	A <sub>0</sub>	6		35	DB <sub>3</sub>
	A <sub>1</sub>	7		34	DB <sub>4</sub>
	A <sub>2</sub>	8		33	DB <sub>5</sub>
	A <sub>3</sub>	9	· 6510	32	DB <sub>6</sub> .
	A <sub>4</sub>	10	6510	31	DB <sub>7</sub>
	A <sub>5</sub>	11		30	Po
	A <sub>6</sub>	12		29	. P₁
	A <sub>7</sub>	13		28	P <sub>2</sub>
•	A <sub>8</sub>	! 14		27	· P <sub>3</sub>
	A <sub>9</sub>	15		26	P <sub>4</sub>
;	A <sub>10</sub>	16		25	P <sub>5</sub>
	A <sub>11</sub>	17		24	P <sub>6</sub>
	A <sub>12</sub>	18		23	P <sub>7</sub>
	A <sub>13</sub>	19		22	A <sub>13</sub>
	v <sub>ss</sub>	20		· 21	A <sub>14</sub>

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**73C** 00036

T-49-17-06

#### 6510 CHARACTERISTICS

#### **MAXIMUM RATINGS**

RATING	SYMBOL	VALUE	UNIT
SUPPLY VOLTAGE	V <sub>CC</sub>	-0.3 to $+7.0$	Vdc
INPUT VOLTAGE	Vin	-0.3 to + 7.0	Vdc •
OPERATING TEMPERATURE	TA	0 to + 70	°C
STORAGE TEMPERATURE	TSTG	-55 to + 150	°C

This device contains input protection against damage due to high static voltages or electric fields; however, precautions should be taken to avoid application of voltages higher than the maximum rating.

### ELECTRICAL CHARACTERISTICS (Vcc = 5.0V $\pm$ 5%, Vss = 0, TA = 0° to + 70°C)

CHARACTERISTIC	SYMBOL	· MIN.	TYP.	MAX.	UNIT
Input High Voltage  Ø <sub>1</sub> , Ø <sub>2(in)</sub> Input High Voltage  RES, P <sub>0</sub> -P <sub>7</sub> IRQ, Data	VIH	Vcc - 0.2 Vss + 2.0	<b>-</b>	Vcc + 1.0V —	Vdc Vdc
Input Low Voltage  Ø <sub>1</sub> , Ø <sub>2(in)</sub> RES, P <sub>0</sub> -P <sub>7</sub> IRQ, Data	VIL	Vss - 0.3 /	<u>-</u>	Vss + 0.2 Vss + 0.8	Vdc · Vdc
Input Leakage Current (Vin = 0 to 5.25V, Vcc = 5.25V) Logic Ø <sub>1</sub> , Ø <sub>2(in)</sub>	lin	<u>-</u>	<u>-</u>	2.5 100	AU, AU,
Three State (Off State) input Current (Vin = 0.4 to 2.4V, Vcc = 5.25V)  Data Lines	ITSI	—	-	10	μA
Output High Voltage ( $I_{OH} = -100\mu$ Adc, $Vcc = 4.75V$ ) Data, A0-A15, R/W, $P_0$ - $P_7$	<b>V</b> OH (	Vss + 2.4	_	-	Vdc
Out Low Voltage (I <sub>OL</sub> = 1.6mAdc, Vcc = 4.75V) Data, A0-A15, R/W, P <sub>0</sub> -P <sub>7</sub>	VOL	-	_	Vss + 0.5	Vdc
Power Supply Current	ICC	_	_	130	mA
Capacitance V <sub>in</sub> = 0, T <sub>A</sub> = 25°C, f = 1 MHz) Logic, P <sub>0</sub> -P <sub>7</sub>	C C <sub>in</sub>	_	_	10	pF
Data A0-A15, R/W Ø₁ Ø₂	C <sub>out</sub> C⊘₁ C⊘₂	 	  30 50	15 12 50 80	

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2294173 COMMODORE SEMICONDUCTOR TCYC PWHØ1 TDHL TDLH VCC-02V VCC-0.2V Ø1 (IN) Ø1 (IN) 0.4V TD -TCYC . VCC-0.2V VCC-0.2 V VCC-02V VCC-0.2 V  $\phi_2$  (IN) Ø<sub>2</sub> (OUT) 0.4V 0.4V 0.4V TR. TR. PWHØ2  $PWHØ_2$ · TF THRW . - TRWS -THRW TRWS -0.2 V 2.0 V 2.0 V . R/W R/W THA THA 2.0 V 2.0 2.0 V 2.0 V ADDRESS ADDRESS FROM MPU FROM MPU 0.8 V 0.8 V V 8.0 TADS -- TADS 2.0 V 2.0 V 2.0 V 2.0 V DATA FROM MEMORY DATA FROM MEMORY 0.8V V8.0 0.8 V TACC TDSU Tosu TACC - THR THR TPDSU TPDSU-2.0V 2.0 V PERIPHERAL DATA PERIPHERAL DATA 0.8V 0.8 V VCC-0.2V VCC-0.2 V ADDRESS ADDRESS ENABLE CONTROL ENABLE CONTROL 0.4V 0.4 V 2.0V 2.0V 2.0 V 2.0 V ADDRESS DATA ADDRESS 0.8 V 0.8 V 0.8 V 0.8 V · TAES TAED - TAES TAED Two Phase Clock Input Format Internal Clock Format TIMING FOR READING DATA FROM MEMORY OR PERIPHERALS

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2294173 COMMODORE SEMICONDUCTOR - TCYC - PWHØ₁ TOLH TDHL VCC-0.2V VCC-0.2V Ø1 (IN) Ø1 (IN) 0.4V TD TCYC TD 2.0V VCC-0.2V VCC-02V VCC-0.2V VCC-0.2V Ø2 (IN) Ø2 (OUT) 0.4V 0.4V - PWHØ2 ŦF PWHØ2 -TR TF TR - TRWS --TRWS R/W R/W 0.8V 0.8V 12.0V ADDRESS 2.0V ADDRESS FROM FROM MPU . 0.8V MPU V8.0 TADS - TADS 2.0V 2.0 V 2.0V 2.0V DATA DATA то MEMORY MEMORY 0.80 **V8.0** V8.0 0.8V - THW ► THW TMDS TMDS T<sub>PDW</sub> -TPDW -2.0V PERIPHERAL PERIPHERAL DATA DATA 0.8V VCC-0.2V VCC-0.2V ADDRESS ADDRESS ENABLE ENABLE CONTROL CONTROL 0.4V 0.4V 2.0V 2.0V 2.0V 2.0V ADDRESS DATA TO MEMORY ADDRESS DATA TO **MEMORY** 0.8V V8.0 V8.0 TAED TAED TAES TAES TDED TDES TDED TDES Two-Phase Clock Input Format **Internal Clock Format TIMING FOR WRITING DATA TO MEMORY OR PERIPHERALS** 

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### AC CHARACTERISTICS

1 MHz TIMING

2 MHz TIMING

**3 MHz TIMING** 

ELECTRICAL CHARACTERISTICS (VCC = 5V  $\pm$  5%, VSS = 0V, T<sub>A</sub> = 0° -70°C) Minimum Clock Frequency = 50 KHz

#### **CLOCK TIMING**

CHARACTERISTIC
Cycle Time
Clock Pulse Width Ø1 (Measured at VCC-0.2V) Ø2
Fall Time, Rise Time (Measured from 0.2V to VCC-0.2V)
Delay Time between Clocks (Measured at 0.2V)

SYMBOL	MIN.	TYP.	MAX.
TCYC	1000		
PWHØ1 PWHØ2	430 470	  -	_
T <sub>F</sub> , T <sub>R</sub>	_	_	25
T <sub>D</sub>	0	_	

		•
MIN.	TYP.	MAX.
500		
215 235	_ _	-
_	_	15
0	_	_

Γ	MIN.	TYP.	MAX.	UNITS
	333		_	ns
ſ	150 160	=	-	ns ns
		_	15	ns
	0	_	-	ns

### READING/WRITE TIMING (LOAD=1 TTL)

	- 4
CHARACTERISTIC	
Read/Write Setup Time from 6510	
Address Setup Time from 6510	
Memory Read Access Time	
Data Stability Time Period	
Data Hold Time-Read	
Data Hold Time-Write	
Data Setup Time from 6510	
Address Hold Time	
R/W Hold Time	
Delay Time, Ø2 negative transition to Peripheral Data valid	
Peripheral Data Setup Time	
Address Enable Setup Time	
Data Enable Setup Time	
Address Disable Hold Time*	
Data Disable Hold Time*	
Peripheral Data Hold Time	

SYMBOL	MIN.	TYP.	MAX.
TRWS	_	100	300
TADS	1	100	300
TACC	-	_	575
Tosu	100	_	
THR	10		
THW	10	30	<u> </u>
TMDS		150	200
THA	10	30	_
THRW	10	30	
T <sub>PDW</sub>	<u> </u>		1
TPDSU	300	<u>l – </u>	
TAES	_	_	75
TDES	_	_	120
TAED	T -	Ŀ	120
TDED	_		130
TPDH		<u> </u>	<u> </u>

MIN.	TYP.	MAX.
_	100	150
	100	150
-	_	300
60		_
10	_	
10	30	
_	75	100
10	30	
10	30	
_	_	150
150	<b>-</b>	-
_	-	75
_	-	120
_	_	120
_		130
20		

MĮN.	TYP.	MAX.	UNITS
_	100	110	ns
	100	125	ns
_	_	170	ns
40	-	_	ns
10	_		ns
10	30	-	ns
_	75	90	ns
10	30	-	ns
10	30		ns
_	_	125	ns
100	-	_	ns
_	T-	75	ns
-	_	120	กร
_	T -	120	ns
_	_	130	ns
10		<u> </u>	ns,

<sup>\*</sup>Note - 1 TTL Load, CL=30 pF

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#### SIGNAL DESCRIPTION

#### Clocks $(\emptyset_1, \emptyset_2)$

The 6510 requires either a two phase non-overlapping clock that runs at the Vcc voltage level, or an external control for the internal clock generator.

#### Address Bus (A<sub>0</sub>-A<sub>15</sub>)

The three state outputs are TTL compatible, capable of driving one standard TTL-load and 130 pf.

#### Data Bus (D<sub>0</sub>-D<sub>7</sub>)

Eight pins are used for the data bus. This is a Bi-Directional bus, transferring data to and from the device and peripherals. The outputs are tri-state buffers capable of driving one standard TTL load and 130 pf.

#### Reset

This input is used to reset or start the microprocessor from a power down condition. During the time that this line is held low, writing to or from the microprocessor is inhibited. When a positive edge is detected on the input, the microprocessor will immediately begin the reset sequence.

After a system initialization time of six clock cycles, the mask interrupt flag will be set and the microprocessor will load the program counter from the memory vector locations FFFC and FFFD. This is the start location for program control.

After Vcc reaches 4.75 volts in a power up routine, reset must be held low for at least two clock cycles. At this time the R/W signal will become valid.

When the reset signal goes high following these two clock cycles, the microprocessor will proceed with the normal reset procedure detailed above.

#### Interrupt Request (IRQ)

This TTL level input requests that an interrupt sequence begin within the microprocessor. The micorprocessor will complete the current instruction being executed before recognizing the request. At that time, the interrupt mask bit in the Status Code Register will be examined. If the interrupt mask flag is not set, the microprocessor will begin an interrupt sequence. The Program Counter and Processor Status Register are stored in the stack. The microprocessor will then set the interrupt mask flag high so that no further interrupts may occur. At the end of this cycle, the program counter low will be loaded from address FFFE, and program counter high from location FFFF, therefore transferring program control to the memory vector located at these addresses.

#### Address Enable Control (AEC)

The Address Bus, R/W, and Data Bus are valid only when the Address Enable Control line is high. When low, the Address Bus, R/W and Data Bus are in a highimpedance state. This feature allows easy DMA and multiprocessor systems.

#### I/O Port (Po-P7)

Eight pins are used for the peripheral port, which can transfer data to or from peripheral devices. The Output Register is located in RAM at Address 0001, and the Data Direction Register is at Address 0000. The outputs are capable at driving one standard TTL load and 130 pf.

#### Read/Write (R/W)

This signal is generated by the microprocessor to control the direction of data transfers on the Data Bus. This line is high except when the microprocessor is writing to memory or a peripheral device.

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### ADDRESSING MODES

ACCUMULATOR ADDRESSING — This form of addressing is represented with a one byte instruction, implying an operation on the accumulator.

IMMEDIATE ADDRESSING — In immediate addressing, the operand is contained in the second byte of the instruction, with no further memory addressing required.

ABSOLUTE ADDRESSING — In absolute addressing, the second byte of the instruction specifies the eight low order bits of the effective address while the third byte specifies the eight high order bits. Thus, the absolute addressing mode allows access to the entire 65K bytes of addressable memory.

ZERO PAGE ADDRESSING — The zero page instructions allow for shorter code and execution times by only fetching the second byte of the instruction and assuming a zero high address byte. Careful use of the zero page can result in significant increase in code efficiency.

INDEXED ZERO PAGE ADDRESSING — (X, Y indexing) — This form of addressing is used in conjunction with the index register and is referred to as "Zero Page, X" or "Zero Page, Y." The effective address is calculated by adding the second byte to the contents of the index register. Since this is a form of "Zero Page" addressing, the content of the second byte references a location in page zero. Additionally, due to the "Zero Page" addressing nature of this mode, no carry is added to the high order 8 bits of memory and crossing of page boundaries does not occur.

INDEX ABSOLUTE ADDRESSING — (X, Y indexing) — This form of addressing is used in conjunction with X and Y index register and is referred to as "Absolute, X," and "Absolute, Y." The effective address is formed by adding the contents of X and Y to the address contained in the second and third bytes of the instruction. This mode allows the index register to contain the index or count value and the instruction to contain the base address. This type of indexing allows any location referencing and the index to modify multiple fields resulting in reduced coding and execution time.

IMPLIED ADDRESSING - In the implied addressing mode, the address containing the operand is implicitly stated in the operation code of the instruction.

**RELATIVE ADDRESSING** — Relative addressing is used only with branch instructions and establishes a destination for the conditional branch.

The second byte of the instruction becomes the operand which is an "Offset" added to the contents of the lower eight bits of the program counter when the counter is set at the next instruction. The range of the offset is — 128 to + 127 bytes from the next

INDEXED INDIRECT ADDRESSING — In indexed indirect addressing (referred to as [Indirect, X]), the second byte of the instruction is added to the contents of the X index register, discarding the carry. The result of this addition points to a memory location on page zero whose contents is the low order eight bits of the effective address. The next memory location in page zero contains the high order eight bits of the effective address. Both memory locations specifying the high and low order bytes of the effective address must be in page zero.

INDIRECT INDEXED ADDRESSING — In indirect indexed addressing (referred to as [Indirect, Y]), the second byte of the instruction points to a memory location in page zero. The contents of this memory location is added to the contents of the Y index register, the result being the low order eight bits of the effective address. The carry from this addition is added to the contents of the next page zero memory location, the result being the high order eight bits of the effective address.

ABSOLUTE INDIRECT — The second byte of the instruction contains the low order eight bits of a memory location. The high order eight bits of that memory location is contained in the third byte of the instruction. The contents of the fully specified memory location is the low order byte of the effective address. The next memory location contains the high order byte of the effective address which is loaded into the sixteen bits of the program counter.

## INSTRUCTION SET - ALPHABETIC SEQUENCE

ADS	Add Memory to Accumulator with Carry
VND	"AND" Memory with Accumulator

Shift left One Bit (Memory or Accumulator) ASL

Branch on Carry Clear BCC Branch on Carry Set BCS

Branch on Result Zero BEQ

Test Bits in Memory with Accumulator Branch on Result Minus BIT вмі

Branch on Result not Zero Branch on Result Plus BNE

Force Break

BRK Branch on Overflow Clear BVC Branch on Overflow Set **BVS** 

CLC

Clear Carry Flag Clear Decimal Mode Clear Interrupt Disable Bit CLD Clear Overflow Flag

CLV Compare Memory and Accumulator CMP Compare Memory and Index X

CPX Compare Memory and Index Y CPY

Decrement Memory by One DEC Decrement Index X by One DEX Decrement Index Y by One DEY

"Exclusive or" Memory with Accumulator EOR

Increment Memory by One Increment Index X by One Increment Index Y by One INC INX

INY

Jump to New Location **JMP** Jump to New Location Saving Return Address

Load Accumulator with Memory LDA LDX

Load Index X with Memory Load Index Y with Memory Shift One Bit Right (Memory or Accumulator) LSR

No Operation NOP

"OR" Memory with Accumulator ORA

Push Accumulator on Stack PHA Push Processor Status on Stack PHP Pull Accumulator from Stack

Pull Processor Status from Stack PLP

Rotate One Bit Left (Memory or Accumulator) ROL Rotate One Bit Right (Memory or Accumulator) ROR

Return from interrupt Return from Subroutine

Subtract Memory from Accumulator with Borrow SBC

Set Carry Flag SEC Set Decimal Mode SED

Set Interrupt Disable Status SEI Store Accumulator in Memory

Store Index X in Memory Store Index Y in Memory

Transfer Accumulator to Index X TAX Transfer Accumulator to Index Y Transfer Stack Pointer to Index X

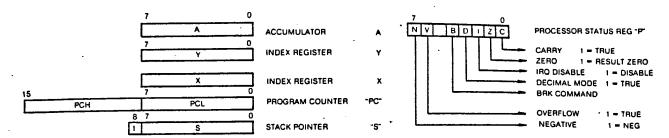
TSX Transfer Index X to Accumulator Transfer Index X to Stack Register

**TXS** Transfer Index Y to Accumulator

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#### PROGRAMMING MODEL



#### INSTRUCTION SET-OP CODES, Execution Time, Memory Requirements

			INSTRUCTIONS			BUTE		taur'			me		4CO			ru.			PR. 1			O, 1			44.			11. I			1. 1		¥۷						PAGE			ONO				
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### APPLICATIONS NOTES

Locating the Output Register at the internal I/O Port in Page Zero enhances the powerful Zero Page Addressing instructions of the 6510.

By assigning the I/O Pins as inputs (using the Data Direction Register) the user has the ability to change the contents of address 0001 (the Output Register) using peripheral devices. The ability to change these contents using peripheral inputs, together with Zero Page Indirect Addressing instructions, allows novel and versatile programming techniques not possible earlier.

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